



09-13-a

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Express Mail No. EL963273053US  
ELM/001 Cont. 14

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant : Glenn J. Leedy  
Application No. : 10/766,557 Confirmation No. : 3092  
Filed : January 27, 2004  
For : METHODS FOR MASKLESS LITHOGRAPHY  
Examiner : Not yet assigned  
Group Art Unit : 2812

New York, New York 10020  
September 10, 2004

Mail Stop Amendment  
Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT

Sir:

In accordance with 37 C.F.R. §§ 1.56 and 1.97,  
applicants wish to call the attention of the Examiner to the  
following documents:

U.S. Patent Documents

Shibata	4,500,905	02/19/1985
Wang, et al.	4,892,753	01/09/1990
Kato, et al.	4,939,568	07/03/1990
Wang, et al.	5,000,113	03/19/1991
Linglain, et al.	5,240,458	08/31/1993
Bantien	5,259,247	11/09/1993
Fujii, et al.	RE 34,893	04/04/1995
Wang, et al.	RE 36,623	03/21/2000
Brix, et al.	6,087,284	07/11/2000
Momohara	6,518,073	02/11/2003

Foreign Patent Documents

Japan	04-196263	07/1992
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### Other Documents

Aboaf, J.A., "Stresses in SiO<sub>2</sub> Films Obtained from the Thermal Decomposition of Tetraethylorthosilicate - Effect of Heat Treatment and Humidity," J. Electrochem. Soc.: Solid State Science; 116(12): 1732-1736 (Dec. 1969).

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Tessier, et al., "An Overview of Dielectric Materials for Multichip Modules," SPE, Electrical & Electronic Div.; (6): 260-269 (1991).

Treichel, et al., "Planarized Low-Stress Oxide/Nitride Passivation for ULSI Devices," J. Phys IV, Colloq. (France), 1 (C2): 839-846 (1991).

Krishnamoorthy, et al., "3-D Integration of MQW Modulators Over Active Submicron CMOS Circuits: 375 Mb/s Transimpedance Receiver -Transmitter Circuit," IEEE Photonics Technology Letters, 2(11): 1288-1290 (November 1995).

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"Miniature Electron Microscopes Without Vacuum Pumps, Self-Contained, Microfabricated Devices with Short

Working Distances, Enable Operation in Air," NASA Tech Briefs, 39-40 (1998).

Partial European Search Report for Application No. EP 02009643 (October 8, 2002).

Copies of the aforementioned documents, which are listed on the accompanying Form PTO-1449 (submitted in duplicate), are enclosed herewith.

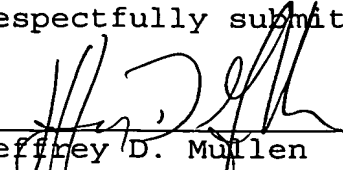
It is respectfully requested that these documents be (1) fully considered by the Patent and Trademark Office during examination of this application; and (2) printed on any patent which may issue on this application. Applicants request that a copy of Form PTO-1449, as considered and initialed by the Examiner, be returned with the next communication.

This Statement is being submitted more than three months from the application filing date but before the mailing date of the first Office Action on the merits.

In accordance with 37 C.F.R. § 1.97(b)(3), submission of this Statement requires no fee. However, if for any reason a fee is due, the Director is hereby authorized to charge payment of any fees required in connection with this Supplemental Information Disclosure Statement to Deposit Account No. 06-1075. A duplicate copy of this statement is transmitted herewith.

An early and favorable action is respectfully  
requested.

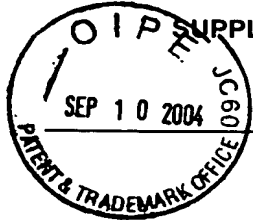
Respectfully submitted,



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FORM PTO-1449

U.S. DEPARTMENT OF COMMERCE  
PATENT AND TRADEMARK OFFICEATTY. DOCKET NO.  
ELM/001 Cont. 14APPLN. NO.  
10/766,557SUPPLEMENTAL INFORMATION DISCLOSURE  
STATEMENT BY APPLICANTAPPLICANTS  
Glenn J. LeedyCONF. NO.  
3092FILING DATE  
January 27, 2004GROUP ART UNIT  
2812

## U.S. PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
	4,500,905	02/19/1985	Shibata	357	68	
	4,939,568	07/03/1990	Kato, et al.	357	75	
	4,892,753	01/09/1990	Wang, et al.	427	579	
	5,000,113	03/19/1991	Wang, et al.	118	723	
	5,240,458	08/31/1993	Linglain, et al.	464	63	
	5,259,247	11/09/1993	Bantien	73	718	
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	6,518,073	02/11/2003	Momohara	438	4	12/10/2001

## FOREIGN PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
						YES	NO
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EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not conformance and not considered. Include copy of this form with next communication to applicant.

<b>FORM PTO-1449</b>  <b>U.S. DEPARTMENT OF COMMERCE</b> <b>PATENT AND TRADEMARK OFFICE</b>  <b>SUPPLEMENTAL INFORMATION DISCLOSURE</b> <b>STATEMENT BY APPLICANT</b>	<b>ATTY. DOCKET NO.</b> ELM/001 Cont. 14	<b>APPLN. NO.</b> 10/766,557
	<b>APPLICANTS</b> Glenn J. Leedy	<b>CONF. NO.</b> 3092
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P.O. Box 1450  
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EXPRESS MAIL CERTIFICATION

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Date of Deposit: September 10, 2004

I hereby certify that this certification and the following papers and fees:

1. Supplemental Information Disclosure Statement (in duplicate);
2. Form PTO-1449 (in duplicate);
3. Copies of twenty-two (22) cited references; and
4. Return postcard

are being deposited with the United States Postal Service "EXPRESS MAIL POST OFFICE TO ADDRESSEE" service under 37 C.F.R. § 1.10 on the date indicated above and are addressed to Mail Stop Amendment, Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450.

Name:

  
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Claire J. Saintil-van Goodman